

Title (en)

A method of forming a TEOS cap layer at low temperature and reduced deposition rate

Title (de)

Verfahren zur Bildung einer TEOS-Kappenschicht bei niedriger Temperatur und verringerter Ablagerungsrate

Title (fr)

Procédé pour former une couche d'encapsulation d'orthosilicate de tétraéthyle à faible température et à taux de dépôt réduit

Publication

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Application

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Abstract (en)

[origin: WO2005024922A1] The present invention discloses a method for forming a silicon dioxide cap layer for a carbon hard mask layer for the patterning of polysilicon line features having critical dimensions of 50 nm and less. To this end, a low temperature plasma-enhanced CVD process is used, in which the deposition rate is maintained low to provide improved controllability of the layer thickness and, thus, of the optical characteristics of the silicon dioxide layer.

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